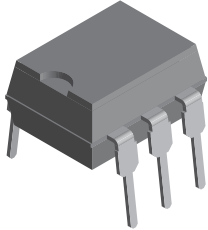
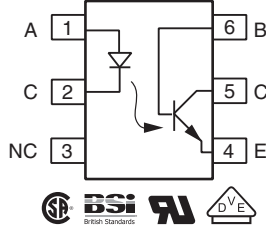


Optocoupler, Phototransistor Output, with Base Connection, 300 V BV_{CE0}



H179004-3



FEATURES

- Good CTR linearity with forward current
- Low CTR degradation
- Very high collector emitter breakdown voltage, $BV_{CE0} = 300\text{ V}$
- Isolation test voltage: 5300 V_{RMS}
- Low coupling capacitance
- High common mode transient immunity
- Phototransistor optocoupler 6 pin DIP package with base connection
- Compliant to RoHS Directive 2002/95/EC and in accordance to WEEE 2002/96/EC


RoHS
COMPLIANT

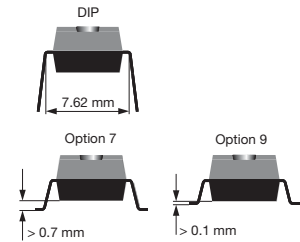
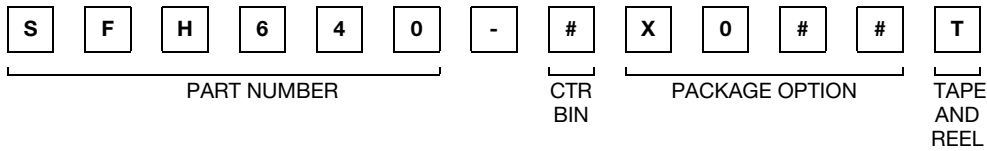
DESCRIPTION

The SFH640 is an optocoupler with very high BV_{CE0} , a minimum of 300 V. It is intended for telecommunications applications or any DC application requiring a high blocking voltage.

AGENCY APPROVALS

- UL1577, file no. E52744 system code H or J, double protection
- DIN EN 60747-5-2 (VDE 0884) available with option 1
- CSA 93751
- BSI IEC 60950; IEC 60065

ORDERING INFORMATION



AGENCY CERTIFIED/PACKAGE	CTR (%)	
	10 mA	
UL, CSA, BSI	63 to 125	100 to 200
DIP-6	SFH640-2	SFH640-3
SMD-6, option 7	SFH640-2X007	SFH640-3X007T ⁽¹⁾
VDE, UL, CSA, BSI	63 to 125	100 to 200
SMD-6, option 9	-	SFH640-3X019T ⁽¹⁾

Notes

- Additional options may be possible, please contact sales office.
- ⁽¹⁾ Also available in tubes, do not put T on the end.

ABSOLUTE MAXIMUM RATINGS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
INPUT				
Reverse voltage		V_R	6.0	V
DC forward current		I_F	60	mA
Surge forward current	$t_p \leq 10\text{ }\mu\text{s}$	I_{FSM}	2.5	A
Total power dissipation		P_{diss}	100	mW



ABSOLUTE MAXIMUM RATINGS (T _{amb} = 25 °C, unless otherwise specified)				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
OUTPUT				
Collector emitter voltage		V _{CEO}	300	V
Collector base voltage		V _{CBO}	300	V
Emitter base voltage		V _{EBO}	7.0	V
Collector current		I _C	50	mA
Surge collector current	t _p ≤ 10 ms	I _C	100	mA
Total power dissipation		P _{diss}	300	mW
COUPLER				
Isolation test voltage between emitter and detector		V _{ISO}	5300	V _{RMS}
			7500	V _{PK}
Isolation resistance	V _{IO} = 500 V, T _{amb} = 25 °C	R _{IO}	≥ 10 ¹²	Ω
	V _{IO} = 500 V, T _{amb} = 100 °C	R _{IO}	≥ 10 ¹¹	Ω
Insulation thickness between emitter and detector			≥ 0.4	mm
Creepage distance			≥ 7	mm
Clearance distance			≥ 7	mm
Comparative tracking index per DIN IEC 112/VDE 0303, part 1		CTI	175	
Storage temperature range		T _{stg}	- 55 to + 150	°C
Operating temperature range		T _{amb}	- 55 to + 100	°C
Soldering temperature ⁽¹⁾	max. 10 s, dip soldering: distance to seating plane ≥ 1.5 mm	T _{sld}	260	°C

Notes

- Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute maximum ratings for extended periods of the time can adversely affect reliability.
- ⁽¹⁾ Refer to reflow profile for soldering conditions for surface mounted devices (SMD). Refer to wave profile for soldering conditions for through hole devices (DIP).

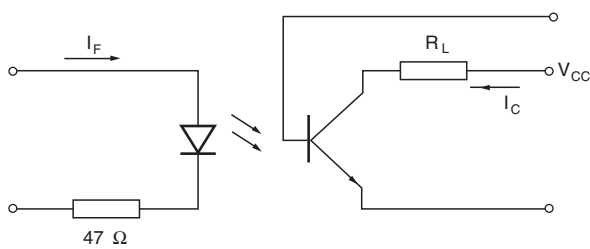
ELECTRICAL CHARACTERISTICS (T _{amb} = 25 °C, unless otherwise specified)							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
INPUT							
Forward voltage	I _F = 10 mA		V _V		1.1	1.5	V
Reverse voltage	I _R = 10 μA		V _R	6			V
Reverse current	V _R = 6 V		I _R		0.01	10	μA
Capacitance	V _F = 0 V, f = 1 MHz		C _O		25		pF
Thermal resistance			R _{thja}		750		K/W
OUTPUT							
Collector emitter breakdown voltage	I _{CE} = 1 mA, R _{BE} = 1 MΩ		BV _{CER}	300			V
Voltage emitter base	I _{EB} = 10 μA		BV _{BEO}	7			V
Collector emitter capacitance	V _{CE} = 10 V, f = 1 MHz		C _{CE}		7		pF
Collector base capacitance	V _{CB} = 10 V, f = 1 MHz		C _{CB}		8		pF
Emitter base capacitance	V _{EB} = 5 V, f = 1 MHz		C _{EB}		38		pF
Thermal resistance			R _{thja}		250		K/W
COUPLER							
Coupling capacitance			C _C		0.6		pF
Saturation voltage collector emitter	I _F = 10 mA, I _C = 3.2 mA	SFH640-2	V _{CEsat}		0.25	0.4	V
	I _F = 10 mA, I _C = 5 mA	SFH640-3	V _{CEsat}		0.25	0.4	V
Collector emitter leakage current	V _{CE} = 200 V, R _{BE} = 1 MΩ		I _{CER}		1	100	nA

Note

- Minimum and maximum values are testing requirements. Typical values are characteristics of the device and are the result of engineering evaluation. Typical values are for information only and are not part of the testing requirements.

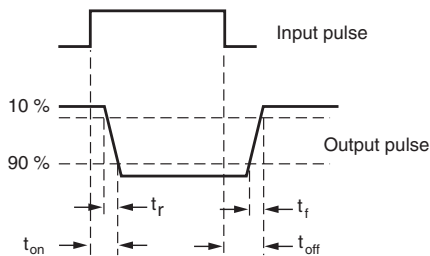
CURRENT TRANSFER RATIO ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
Current transfer ratio	$I_F = 10\text{ mA}$, $V_{CE} = 10\text{ V}$	SFH640-2	I_C/I_F	63		125	%
	$I_F = 1\text{ mA}$, $V_{CE} = 10\text{ V}$	SFH640-2	I_C/I_F	22	45		%
	$I_F = 10\text{ mA}$, $V_{CE} = 10\text{ V}$	SFH640-3	I_C/I_F	100		200	%
	$I_F = 1\text{ mA}$, $V_{CE} = 10\text{ V}$	SFH640-3	I_C/I_F	34	70		%

SWITCHING CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)							
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT	
Turn-on time	$I_C = 2\text{ mA}$, $R_L = 100\text{ }\Omega$, $V_{CC} = 10\text{ V}$	t_{on}		5		μs	
Rise time	$I_C = 2\text{ mA}$, $R_L = 100\text{ }\Omega$, $V_{CC} = 10\text{ V}$	t_r		2.5		μs	
Turn-off time	$I_C = 2\text{ mA}$, $R_L = 100\text{ }\Omega$, $V_{CC} = 10\text{ V}$	t_{off}		6		μs	
Fall time	$I_C = 2\text{ mA}$, $R_L = 100\text{ }\Omega$, $V_{CC} = 10\text{ V}$	t_f		5.5		μs	

TYPICAL CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)


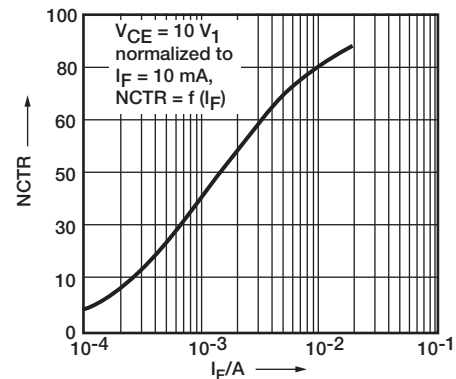
isfh640_01a

Fig. 1 - Switching Times Measurement Test Circuit and Waveform



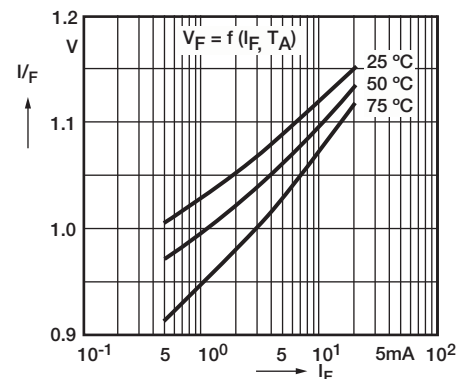
isfh640_01b

Fig. 2 - Switching Times Measurement Test Circuit and Waveform



isfh640_02

Fig. 3 - Current Transfer Ratio (typ.)



isfh640_03

Fig. 4 - Diode Forward Voltage (typ.)

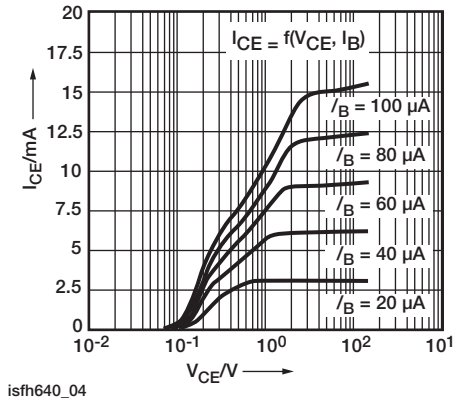


Fig. 5 - Output Characteristics (typ.)

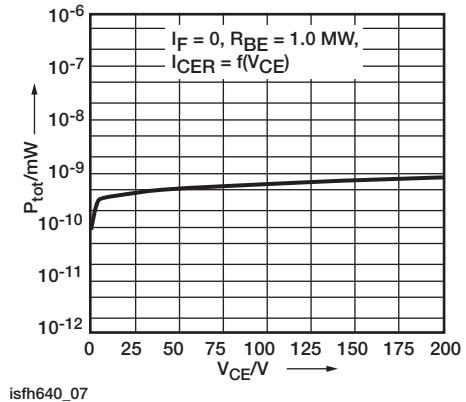


Fig. 8 - Collector-Emitter Leakage Current (typ.)

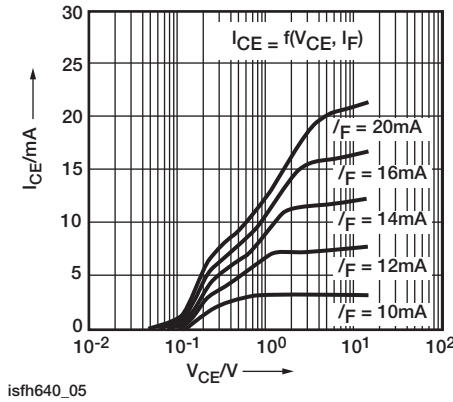


Fig. 6 - Output Characteristics (typ.)

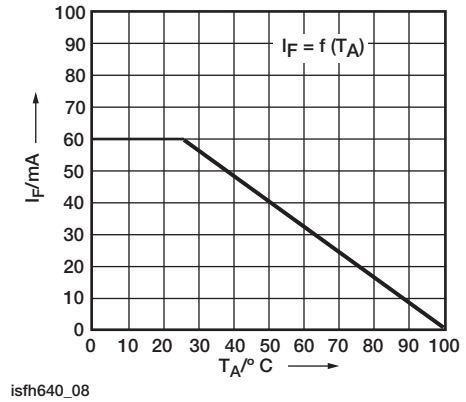


Fig. 9 - Permissible Loss Diode

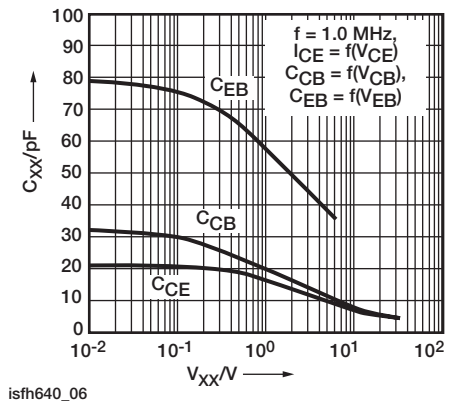


Fig. 7 - Transistor Capacitances (typ.)

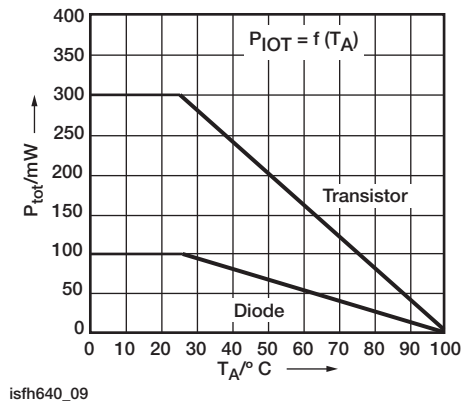
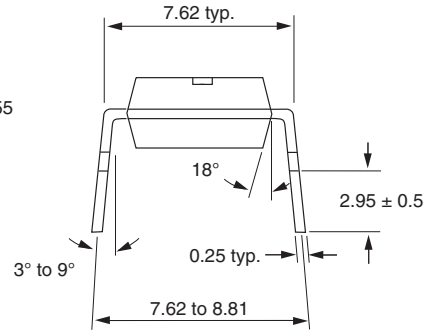
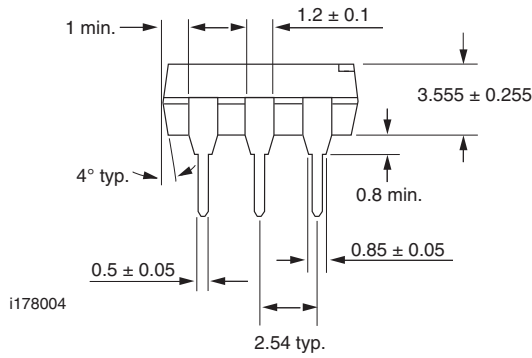
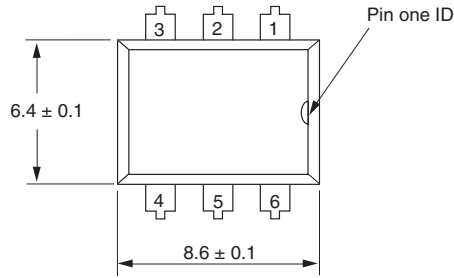
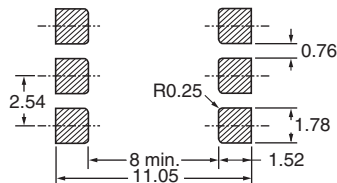
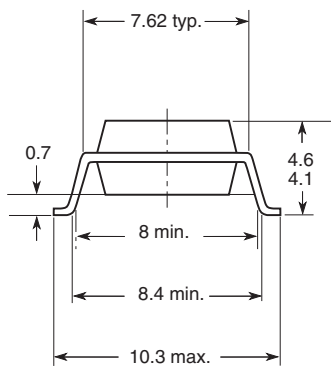


Fig. 10 - Permissible Power Dissipation

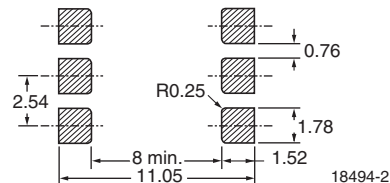
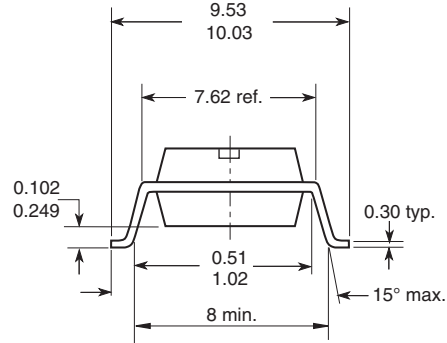
PACKAGE DIMENSIONS in millimeters



Option 7



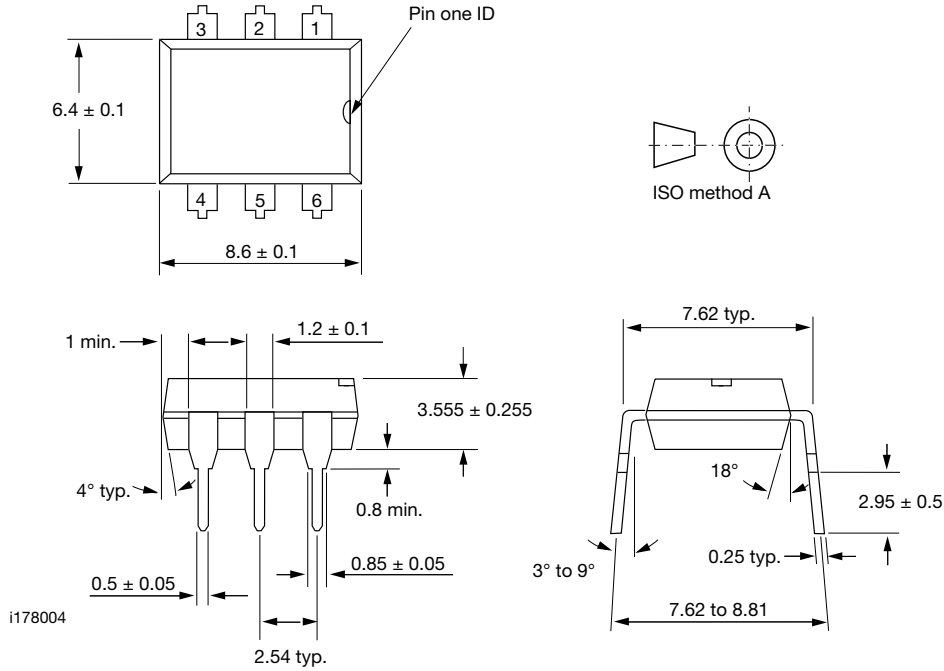
Option 9





DIP-6A

PACKAGE DIMENSIONS in inches (millimeters)



Note

The information in this document provides generic information but for specific information on a product the appropriate product datasheet should be used.



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